

Stacking orders induced direct band gap in bilayer

MoSe<sub>2</sub>-WSe<sub>2</sub> lateral heterostructures

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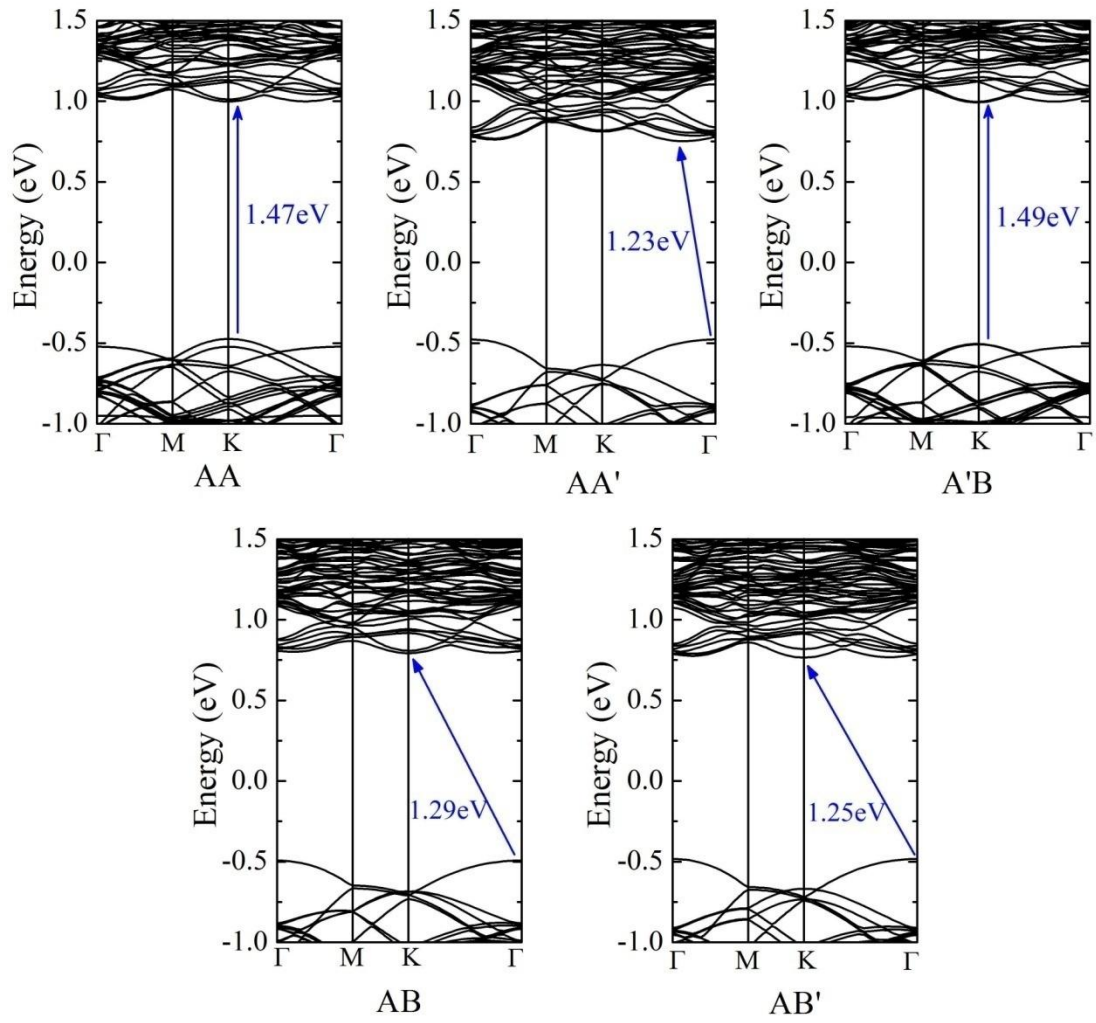


Figure S1 Band structures of AA, AA', A'B, AB, and AB' stacked bilayer

MoSe<sub>2</sub>-WSe<sub>2</sub> lateral heterostructures in the case of B1.

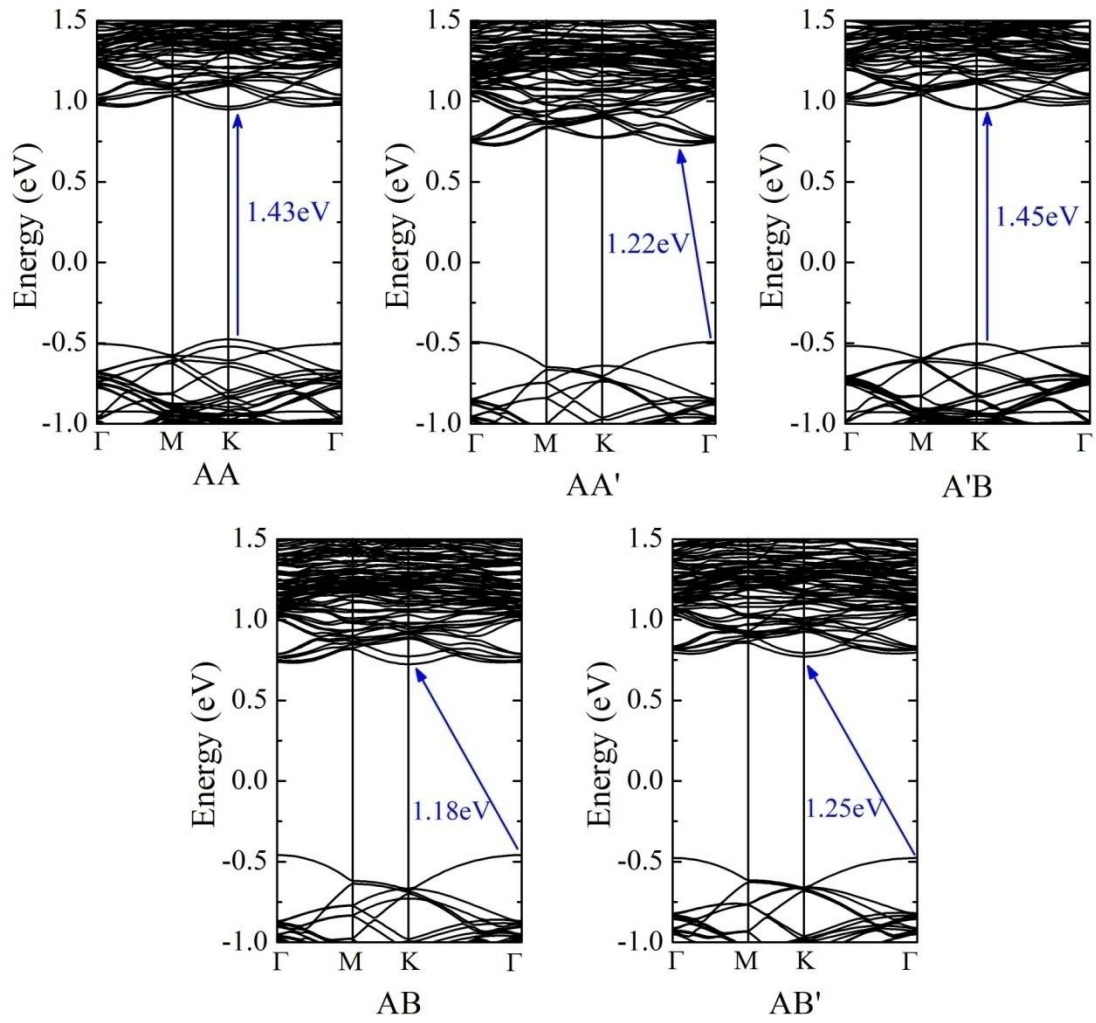


Figure S2 Band structures of AA, AA', A'B, AB, and AB' stacked bilayer

MoSe<sub>2</sub>-WSe<sub>2</sub> lateral heterostructures in the case of B3.